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**IN THE CLAIMS:**

✓✓✓✓✓✓  
Please cancel claims 1, 4, 5, 10, 13 and 14.

Please amend claims 2, 3, and 6 as follows:

Sub B' ✓  
2. (Amended) A semiconductor device comprising:

a substrate having a front surface and a rear surface;

fig. 12 E  
an aluminum nitride insulating film [comprising aluminum, nitrogen and oxygen] containing therein at least one of boron, silicon, carbon, and oxygen provided [on] under said rear surface of the substrate; and

a transistor provided over said front surface of the substrate, said transistor having at least a channel formation region comprising crystalline silicon, a gate insulating film adjacent to said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween.

Sub E17  
fig. 12 E  
3. (Amended) A semiconductor device comprising:

a substrate having a front surface and a rear surface;

an aluminum nitride insulating film [comprising aluminum, nitrogen and oxygen] containing therein at least one of boron, silicon, carbon, and oxygen provided [on] under said rear surface of the substrate; and

a transistor provided over said front surface of the substrate, said transistor having at least a channel formation region comprising crystalline silicon, a gate insulating film adjacent to said channel formation region, and a gate electrode

adjacent to said channel formation region with said gate insulating film interposed therebetween,

wherein said aluminum nitride insulating film [comprising aluminum nitride] has a thermal conductivity of 0.6 W/cm·K or higher.

Subt B<sup>2</sup>  
A<sup>1</sup>  
cont

6. (Amended) An active matrix type liquid crystal display comprising:  
a substrate having a front surface and a rear surface;

an aluminum nitride insulating film [comprising aluminum, nitrogen and oxygen] containing therein at least one of boron, silicon, carbon, and oxygen provided [on] under said rear surface of the substrate; and

fig. 12E

a transistor provided over said front surface of the substrate, said transistor having at least a channel formation region comprising crystalline silicon, a gate insulating film adjacent to said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween.

Subt B<sup>4</sup>

Please add new claims 19-30 as follows:

A<sup>2</sup>  
fig. 12E

--19. A semiconductor device comprising:

a substrate having a front surface and a rear surface;

an aluminum nitride insulating film containing therein at least one of boron, silicon, carbon, and oxygen provided over said front surface of the substrate; and

a transistor provided over said aluminum nitride insulating film, said transistor having at least a channel formation region comprising crystalline silicon,

~~B~~  
a gate insulating film adjacent to said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween.

Sub E3

20. A semiconductor device comprising:

a substrate having a front surface and a rear surface;

an aluminum nitride insulating film containing therein at least one of boron, silicon, carbon, and oxygen provided over said front surface of the substrate; and

a transistor provided over said aluminum nitride insulating film, said transistor having at least a channel formation region comprising crystalline silicon, a gate insulating film adjacent to said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween,

wherein said aluminum nitride insulating film has a thermal conductivity of 0.6 W/cm·K or higher.

2  
A  
cont  
fig. 12E

Subt B5

21. An active matrix type liquid crystal display comprising:

a substrate having a front surface and a rear surface;

an aluminum nitride insulating film containing therein at least one of boron, silicon, carbon, and oxygen provided over said front surface of the substrate; and

a transistor provided over said aluminum nitride insulating film, said transistor having at least a channel formation region comprising crystalline silicon, a gate insulating film adjacent to said channel formation region, and a gate electrode

fig. 12E

~~B~~  
adjacent to said channel formation region with said gate insulating film interposed therebetween.

*Sub E31*  
*A<sup>2</sup> cont*  
*fig. 12E*  
22. A semiconductor device comprising:  
a substrate having a front surface and a rear surface;  
an aluminum nitride insulating film containing therein at least one of boron, silicon, carbon, and oxygen provided under said rear surface of the substrate; and  
a transistor provided over said front surface of the substrate, said transistor having at least a channel formation region comprising crystalline silicon, a gate insulating film adjacent to said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween,  
wherein aluminum to nitrogen ratio in said aluminum nitride insulating film is in the range of 0.9 to 1.4.

*fig. 12E*  
23. A semiconductor device comprising:  
a substrate having a front surface and a rear surface;  
an aluminum nitride insulating film containing therein at least one of boron, silicon, carbon, and oxygen provided under said rear surface of the substrate; and  
a transistor provided over said front surface of the substrate, said transistor having at least a channel formation region comprising crystalline silicon, a gate insulating film adjacent to said channel formation region, and a gate electrode

sub E31 adjacent to said channel formation region with said gate insulating film interposed therebetween,

wherein said aluminum nitride insulating film has a thermal conductivity of 0.6 W/cm·K or higher, and

wherein aluminum to nitrogen ratio in said aluminum nitride insulating film is in the range of 0.9 to 1.4.

24. A semiconductor device comprising:

a substrate having a front surface and a rear surface;

an aluminum nitride insulating film containing therein at least one of boron, silicon, carbon, and oxygen provided over said front surface of the substrate; and

fig. 12E a transistor provided over said aluminum nitride insulating film, said transistor having at least a channel formation region comprising crystalline silicon, a gate insulating film adjacent to said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween,

wherein aluminum to nitrogen ratio in said aluminum nitride insulating film is in the range of 0.9 to 1.4.

25. The device of claim 19 wherein said substrate is a glass substrate.

26. The device of claim 20 wherein said substrate is a glass substrate.

sub G2 27. [The device] of claim 21 wherein said substrate is a glass substrate.